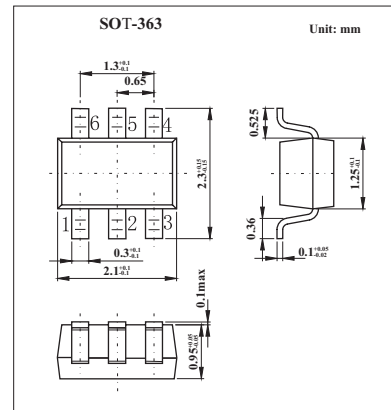


Silicon Schottky Diode

BAT62-08S;BAT62-09S

■ Features

- Low barrier diode for detectors up to GHz frequencies



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Diode reverse voltage	V_{RM}	40	V
Forward current	I_F	20	mA
Total power dissipation; $T_s \leq 105^\circ\text{C}$	P_{FM}	100	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +150	$^\circ\text{C}$
Junction - soldering point ¹⁾	R_{thJS}	≤ 450	K/W
BAT62-08S		≤ 450	
BAT62-09S		$\leq \text{tbd}$	

Note

1. For calculation of R_{thJA} please refer to Application Note Thermal Resistance

■ Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	I_R	$V_R = 40\text{ V}$			10	$\mu\text{ A}$
Forward voltage	V_F	$I_F = 2\text{ mA}$		0.58	1	V
Forward voltage matching ²⁾	ΔV_F	$I_F = 2\text{ mA}$			20	mV

Note

2. ΔV_F is the difference between lowest and highest V_F in a multiple diode component.

■ Marking

Type	BAT62-08S	BAT62-09S
Marking	62s	69s